IN THE SPECIFICATION

Please amend the specification as follows:

Please amend the paragraph beginning at page 1, line 3 as follows.

This application is related to the following commonly assigned U.S. patent application which are herein incorporated by reference in their entirety:
"Output Prediction Logic Circuits With Ultra-Thin Vertical Transistors and Methods of Formation," U.S. Application Serial Number 10/164,611, filed on June 10, 2002; "Micro-Mechanically Strained Semiconductor Film," U.S. Application Serial Number 10/379,749, filed on March 5, 2003 ~~(Attorney Docket 1303.089US1)~~; "Localized Strained Semiconductor on Insulator," U.S. Application Serial Number 10/425,797, filed on April 29, 2003, ~~(Attorney Docket 1303.093US1)~~; "Strained Semiconductor By Wafer Bonding with Misorientation," U.S. Application Serial Number 10/425,484, filed on April 29, 2003, ~~(Attorney Docket 1303.095US1)~~; "Micromechanical Strained Silicon By Wafer Bonding," U.S. Application Serial Number 10/431,137, filed on May 7, 2003, ~~(Attorney Docket 1303.100US1)~~; and "Strained Si/SiGe Structures by Ion Implantation," U.S. Application Serial Number 10/431,134, filed on May 7, 2003. ~~, (Attorney Docket 1303.094US1).~~

Please amend the paragraph beginning at page 16, line 6 as follows.

FIG. 3B is a side cross-section of the structure depicted in FIG. 3A after further processing to form a strained Si/SiGe/SOI island according to an embodiment. After the isotropic etch forms the bubble recess 332, an oxidation process is carried out to vertically isolate an SSOI active area which will become the relaxed region 318 ~~334~~ by the formation of an MFOX 336 or an FMFOX 336. In one embodiment, the oxidation process is carried out with the protective layer 314 and the spacers 330 in place, followed by a nitride etch to remove them.

Please amend the paragraph beginning at page 16, line 13 as follows.

Similar to the bubble recess 332, the size and shape of the MFOX 336 or the FMFOX 336 is also depicted in arbitrary shape and size. The actual size and shape of the MFOX 336 or the FMFOX 336 will be influenced by etch and oxidation conditions according to a process integration. One characteristic of forming the MFOX 336 or the FMFOX 336, requires an oxidation process that leaves the SSOI active area 318 ~~334~~ firmly attached to the substrate 310 through the MFOX 336 or the FMFOX 336. By this process, oxidation is sufficient to vertically isolate the SSOI active area 318 ~~334~~ from the substrate 310 to create an SOI structure. Processing conditions can be ascertained by ordinary experimentation.

Please amend the paragraph beginning at page 16, line 22 as follows.

The oxidation process affects the integrity of the SSOI active area 318 ~~334~~. For a 0.25-micron CD ~~338~~ process, the SSOI active area 318 ~~334~~ has a height ~~340~~ in a range from about 0.1 micron to about 0.15 microns. Alternatively, for a 0.15 micron CD process, the SSOI active area 318 ~~334~~ has a height ~~340~~ in a range from about 0.07 microns to about 0.12 microns.

Please amend the paragraph beginning at page 16, .line 27 as follows.

According to an embodiment, the formation of the MFOX 336 or the FMFOX 336 is carried out under conditions to prevent destructive stresses in the newly formed SSOI active area 318 ~~334~~. One of ordinary skill in the art can read this disclosure and by routine experimentation, conduct the minifield oxidation without causing destructive stresses in the SSOI active area 318 ~~334~~.

Please amend the paragraph beginning at page 17, line 3 as follows.

After formation of the MFOX 336 or the FMFOX 336, a strained silicon layer is formed above the SSOI active area which may now be viewed as a relaxed region 318 according to processing embodiments disclosed herein. This process flow path includes what may be referred to as a "top-down" formation of the strained silicon layer 316, as ion implantation 317 is used. In the next embodiment, a "bottom-up" formation of a ~~stresses~~ stressed silicon film is disclosed.